# RF and Feedback Developments at the ESRF

G. Gautier, N. Guillotin, <u>J. Jacob</u>, J.-M. Koch, J.-M. Mercier, G. Naylor, E. Plouviez, J.-L. Revol, V. Serrière

**ESRF** 

Thanks also to many other colleagues at the ESRF

Three-Way Meeting 2008 APS – Argonne National Laboratory, March 14 – 17, 2008

## Existing 352.2 MHz RF system





#### Undamped HOM



- 2 out of 3 installed klystrons needed to feed the 6 cavities at 200 mA
- ⇒ 1 klystron available for the cavity power test stand or to back up operation for any bunch filling mode

3 Way Meeting, Argonne, March 17-19, 2008

RF and Feedback Developments at ESRF

J. Jacob, page 2

#### RF operation at 200 mA with safety margin

#### Nominal configuration at 200 mA:

- ➤TRA0 on booster cavities 1,2
- ➤TRA1 on SR cavities 1,2,3,4
- ➤TRA3 on SR cavities 5,6

#### ≻TRA2:

- available for the teststand
- can be switched to replace TRA0 or TRA1 when they have to be shut down

#### 200 mA in case of TRA3 fault:

- TRA1 on SR cavities 1,2TRA2 on SR cavities 3,4
- Cavities 5,6 not powered



## Mastering instabilities at 200 mA

- TCBI Transverse Coupled Bunch Instabilities
  - $\ensuremath{\mathfrak{T}}$  Emittance increase  $\rightarrow$  loss in brilliance
    - Resistive wall instability
    - Ion trapping
    - $\rightarrow$  Mastered by an increased chromaticity
    - Transverse cavity HOM are masked
- LCBI Longitudinal Coupled Bunch Instabilities
  - The Energy spread  $\rightarrow$  loss in brilliance, mainly for higher harmonics of undulator radiation
    - Instabilities driven by longitudinal HOM from 6 five-cell Cu cavities for I<sub>beam</sub>
       50 ... 130 mA, depending on T<sub>cav</sub>
    - $\rightarrow$  Stabilisation by Landau damping thanks to transient beam loading from non-symmetric fractional filling  $\rightarrow$  200 mA in 1/3 et 2/3 filling
    - $\rightarrow$  1998: Improved **Cavity temperature regulation** T<sub>cav</sub> = T<sub>set</sub> ± 0.05°C, for a precise control of the HOM frequencies

 $\Rightarrow$  Stable beam at 200 mA in uniform and symmetrical 2 x 1/3 filling

### Further Current Upgrade



#### • 300 mA

- Achieved in Machine Physics test in December 2006
- Foreseen in USM after tests with individual beam lines in 2008/2009

#### • 500 mA

- Not scheduled for the coming accelerator upgrade
- Subject to R&D for the coming 10 years, in preparation of a possible later upgrade
- Any new RF design will have to be compatible with a possible increase to 500 mA

#### Increase to 300 mA



- No intrinsic limitation: neither in RF power, nor from thermal or radiation load
- > However, since 2003 unsuccessful search for a stable working point
  - $\rightarrow$  HOM driven LCBI above 200 ... 250 mA for any T<sub>cav</sub>
- ⇒ End of 2004: Decision to implement a digital bunch-by-bunch feedback system (already reported at last 3 WM in June 2006)
  - LFB (Longitudinal Feedback): to damp HOM driven LCBI
  - TFB (Transverse Feedback): allows operation at zero chromaticity and to damp ion instability at 300 mA
  - Goal: deliver 300 mA to users for limited periods of time in 2008 / 2009
- → December 2006: 300 mA of stable beam successfully stored during machine physics shifts thanks to LFB

# Part I

## Bunch-by-Bunch Digital Feedback Systems 1. LFB 2. TFB

R



3 Way Meeting, Argonne, March 17-19, 2008

## **LFB** figures

R F

- Highly sensitive bunch phase measurement
  - > 1 fs/turn
  - $\Rightarrow$  minimum feedback kick: 4.7 V, well within 600 V kicker spec
- 14 bit ADC:  $\Delta \tau_{max} = \pm 8 \text{ ps}$
- Efficient pre-filtering of spurious signals not related to the unstable synchrotron oscillations:
  - Mode 0 oscillation, beam loading phase transients, injected beam oscillation...
- ESRF naturel longitudinal damping time

 $\succ$   $\tau_s = 3.6 \text{ ms}$ 

- Phase measurement requires a numerical differentiation to compute proper voltage kick: FIR centered on  $f_s \Rightarrow$  limits active damping time:
  - $\succ$   $\tau_{LFB} = 0.5 \text{ ms} \approx \tau_s / 7$
  - ⇒ Allowed to store 300 mA, but Combination of HOM control by Cavity Temperature regulation and LFB damping required !

## FPGA – digital signal processor





#### **Bunch by bunch feedback:**

- parallel processing of all 992 bunches
- processes shifted by  $T_{rf} = 2.84 ns$
- Each process sequenced at  $T_0 = 2.8 \ \mu s$

#### Virtex-II from Xilinx

- ➢ 100 Gops
- Code development with System Generator (Xilinx / The MathWorks)
- Data transfer in and out:
- Four 14 bit ADC channels
   4 x 88 MHz
- One 14 bit DAC (DDR) at 352 MS/s
- ➢ Fast DDR2 RAM 64 MB



3 Way Meeting, Argonne, March 17-19, 2008

LFB: Grow-Damp measurements to tune HOM



3 Way Meeting, Argonne, March 17-19, 2008

RF and Feedback Developments at ESRF

R\I

#### Transverse feedback - TFB



## Vertical kicker layout



- Kicker design: relatively straightforward but HV issues in 4x10mA filling...
- Vertical kicker strength: low (typical cleaning with a 25V/cm field)
- Position measurement resolution demanding; 4µm over 200 MHz of bandwidth required to preserve 20 pm vertical emittance

### Horizontal kicker layout



- Half view:
- Stripline
- U shape to increase the shunt impedance

- Horizontal kicker strength: demanding due to the large spurious kick of the injection (1.5 mm for  $\beta$ =36m); it will limit the damping time.
- Signal processing : processing speed and power similar to the longitudinal case.

3 Way Meeting, Argonne, March 17-19, 2008

## **TFB** figures

- Turn by turn resolution:
   4µm at .2mA/bunch (200mA)
- Loop filter:

Vertical: 8 taps FIR, 3 SR revolution periods Horizontal:7 taps FIR, 3 SR revolution periods Simplest shape: sine shape, no windowing

• Damping time:

Vertical system: 20 turns (50 μs) *limited by the algorithm latency, still 20 dB gain margin* 

Horizontal system: 100 turns (280 µs)

limited by the ratio between the single turn kick amplitude and the amplitude of the injection oscillation due to the kicker bump imperfect closure.

#### TFB - some results

- Damping of resistive wall instability
  - > 200 mA with  $\xi_x = 0$  and  $\xi_z = 0$
- TFB<sub>z</sub> against vertical blow up due to ion trapping in uniform fill
  - > At 300 mA:
    - $\diamond~{\sf TFB}_{\sf z}$  = OFF: ion trapping  $\rightarrow$  vertical blow up  $\rightarrow$  after 20 min beam loss
    - ♦ TFB<sub>z</sub> = ON: vertical blow up limited to  $\varepsilon_z$  = 80 pm
  - > At 200 mA in USM:
    - $\diamond~\epsilon_z: 35 \rightarrow 25$  pm, applied since mid 2007
- At given chromaticity: Increase of single bunch head tail instability thresholds by a factor 2.5 to 3



## Part II

#### ESRF RF upgrade for the coming decade

3 Way Meeting, Argonne, March 17-19, 2008

### Summary / tests with 300 mA at ESRF



## RF:11 MV necessary

for Robinson stability

**R**F

All 3 transmitters in operation ⇒ no margin for test stand or in case of equipment failure

#### LFB:

 Stabilisation of HOM up to 300 mA

**TFB** vertical

 Needed to control beam blow up due to ion trapping

3 Way Meeting, Argonne, March 17-19, 2008

RF and Feedback Developments at ESRF

J. Jacob, page 19

#### Existing system

At 300 mA: all SR transmitters are needed

- TRA1  $\rightarrow$  Cavities 1 & 2
- TRA2  $\rightarrow$  Cavities 3 & 4
- TRA3  $\rightarrow$  Cavities 5 & 6

 $\Rightarrow$  No spare transmitter = no safety margin

- Re-establishing a safety margin at 300 mA would require 2 more 1.3 MW transmitters:
  - $\rightarrow$  One to back up TRA0 (booster), TRA1 and TRA2 (SR)
  - $\rightarrow$  One to back up TRA3 (SR)

#### Transmitter upgrade

- Existing RF transmitters:
  - Only one klystron supplier left
  - These klystrons are particularly subject to instabilities: none is presently in operation at ESRF
- Proposed upgrade with Solid State Amplifiers (SSA):
  - Replace klystron transmitters with SSA
  - $\succ$  SSA highly modular  $\Rightarrow$  redundant  $\Rightarrow$  intrinsically reliable
  - Good experience at SOLEIL, yet still R&D to find even better transistors
  - > 20 dB less phase noise
  - > No HV
  - No X rays
  - Easy maintenance
  - Likely to become the new standard for high power CW RF applications

### **Solid State Amplifiers at SOLEIL**





- $\leftarrow$  50 kW tower:
  - tested at 45 kW
  - normally operated up to 40 kW
  - ↓ 8 towers operated at 2 x [150 to 160 kW]



#### Photos: Courtesy SOLEIL

3 Way Meeting, Argonne, March 17-19, 2008

RF and Feedback Developments at ESRF

J. Jacob, page 22

#### **Solid State Amplifiers at SOLEIL**



#### **R&D** for better transistors



- GOAL: raise the operation power from 40 to 45 kW/tower
  - SOLEIL booster: SEMELAB transistors VDMOS D1029UK05
  - SOLEIL SR: Improved performance with POLYFET LDMOS LR301 (V4)
  - Prototype tests at SOLEIL with BLF 369 from NXP:
    - ♦ Very robust device
    - Draw back: larger capacitances require larger compensating capacitors operated at high temperature, solutions under development at SOLEIL
    - ♦ BLF 369 is presently the best candidate for an ESRF amplifier
  - New BLF 574 from NXP: first samples under test at SOLEIL
    - 50 V bias instead of 30 V will bring 10 % better efficiency and reduce the losses
    - ◊ Expected to be more resistant

Procurement of solid state amplifiers

- Collaboration with SOLEIL
- Some companies already interested in supplying complete SSA systems:
  - One company: possible license agreement with SOLEIL
  - Another company proposing its own design

### New Cavities for the ESRF

- Optimized for high beam current
  - At least 1 coupler per cell (instead of existing 2 couplers / 5-cell-cavity)
     ⇒ Single cell cavities
  - Strong HOM damping for unconditional stability at 300 mA without active HOM damping
  - Design goal including necessary margins:
    - ♦ 500 mA in terms of power
    - ♦ 1000 mA in terms of HOM damping

## Single cell NC HOM damped cavity



•

RF and Feedback Developments at ESRF

460 MHz

### Multibunch – HOM driven LCBI



3 Way Meeting, Argonne, March 17-19, 2008

#### Planned RF upgrade / coming 8 years



- Replacement of all 6 SR five-cell cavities with 6 x 3 new single cell HOM damped cavities
- 9 MV / 300 mA: 18 cavities at 120 kW
- 18 solid state amplifiers
  - ◊ 3 towers x 45 kW = 135 kW: sufficient margin
  - R&D for improved transistors therefore essential
  - Note that currents above 300 mA will be possible by adding a 4<sup>th</sup> tower to each SR amplifier
- 4 amplifiers x 3 towers for the booster cavities
  - Output Can be switched ON/OFF within 10 seconds: better adapted to frequent top up operation than klystrons

#### Scheme for additional long beamline ID7



#### 7m straight with 3 new single cell cavities



- Transform Cells 7 and 23 into long straights
- Replace SR cavity 3 with 3 single cell cavities in the middle of cell 7
  - Creates new space for a long beam line ID7 with 2 ID's
- Replace SR cavity 4 with 3 single cell cavities in the middle of cell 23
  - Keeping existing 2 canted undulators in ID23: just insert 3.2 m of RF
- Scheme could also be applied to cells 5 / 21 and cells 9 / 25

